

HAT1021R

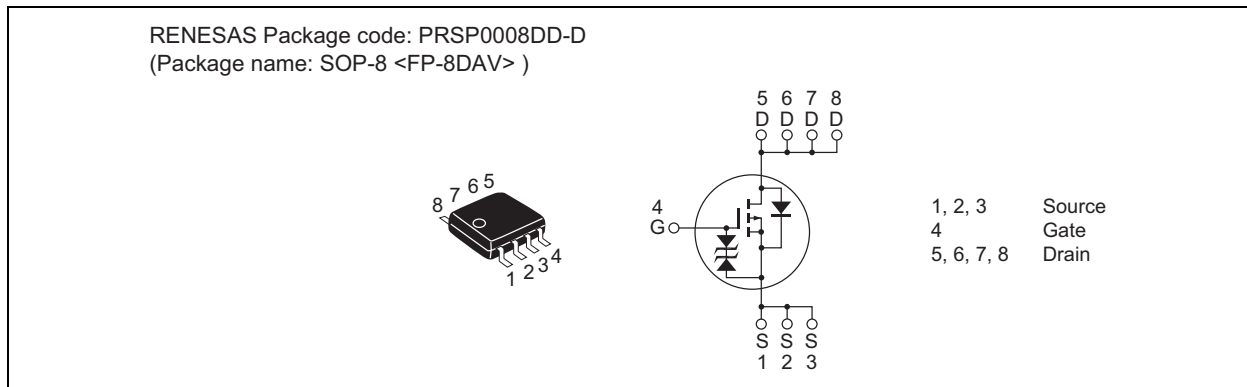
Silicon P Channel Power MOS FET
High Speed Power Switching

REJ03G1144-0600
(Previous: ADE-208-475D)
Rev.6.00
Sep 07, 2005

Features

- Low on-resistance
- Capable of 2.5 V gate drive
- Low drive current
- High density mounting

Outline



Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Value	Unit
Drain to source voltage	V _{DSS}	-20	V
Gate to source voltage	V _{GSS}	±10	V
Drain current	I _D	-5.5	A
Drain peak current	I _{D (pulse)} ^{Note 1}	-44	A
Body-drain diode reverse drain current	I _{DR}	-5.5	A
Channel dissipation	P _{ch} ^{Note 2}	2.5	W
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

Notes: 1. PW ≤ 10 μs, duty cycle ≤ 1%

2. When using the glass epoxy board (FR4 40 × 40 × 1.6 mm), PW ≤ 10 s

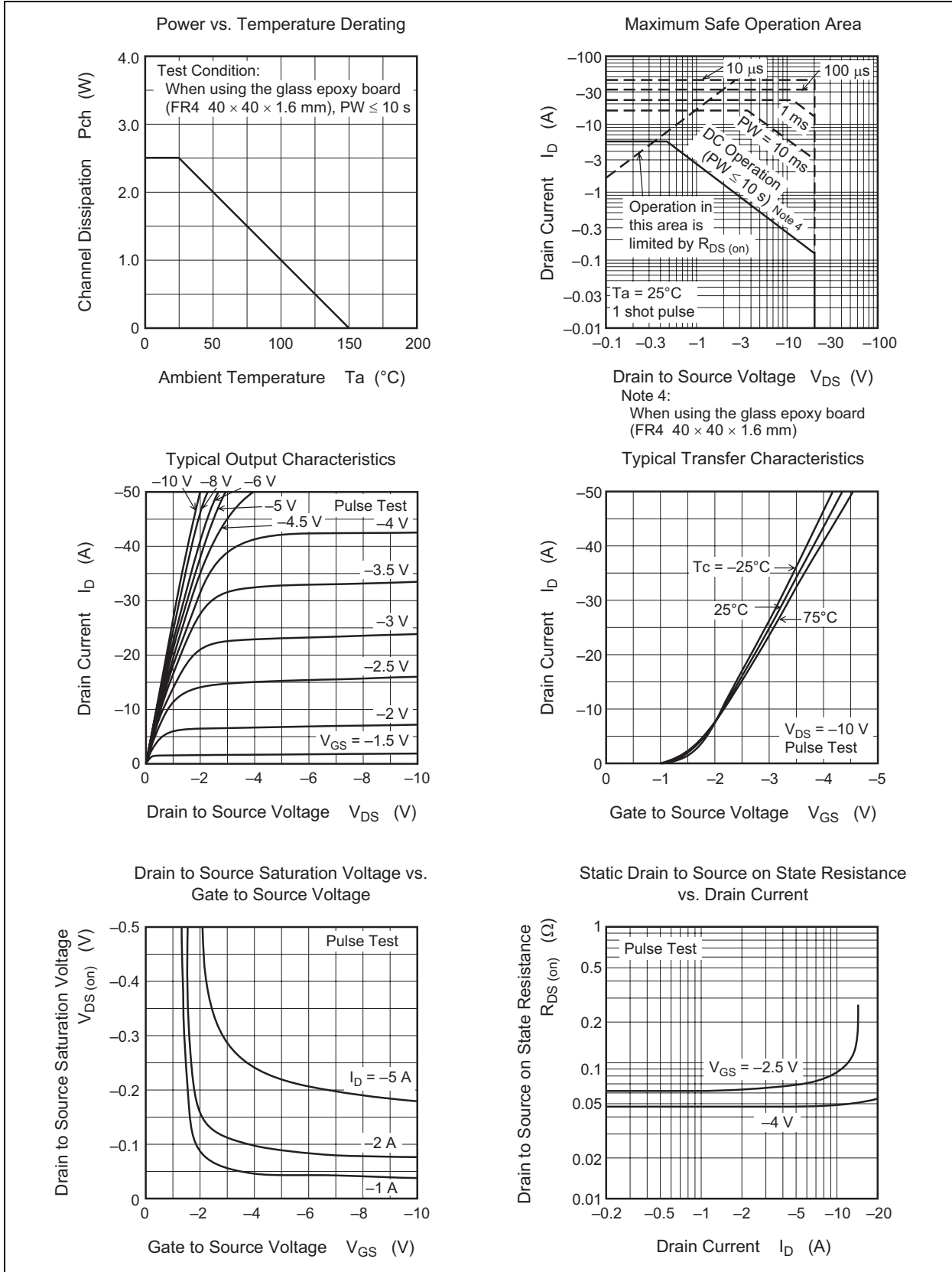
Electrical Characteristics

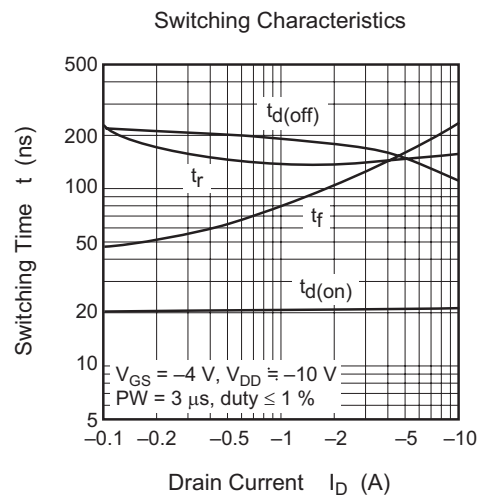
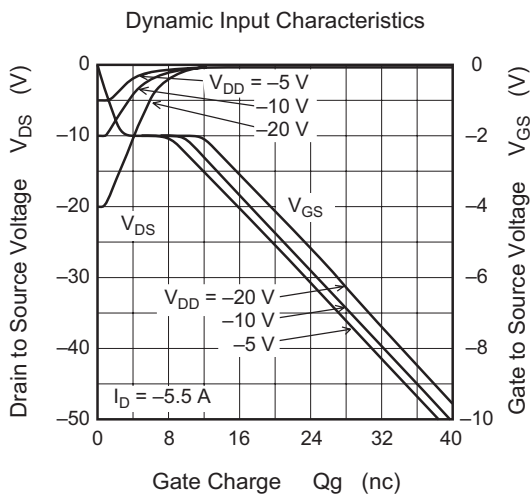
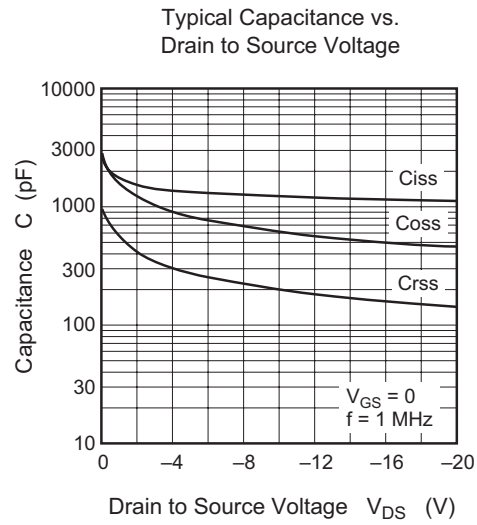
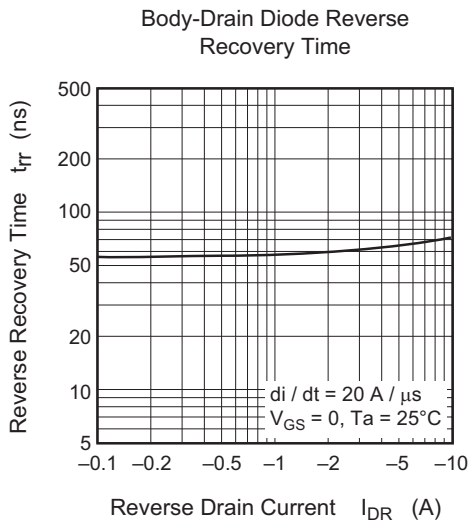
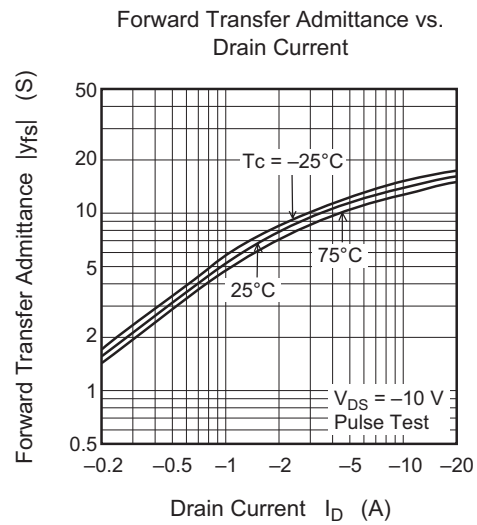
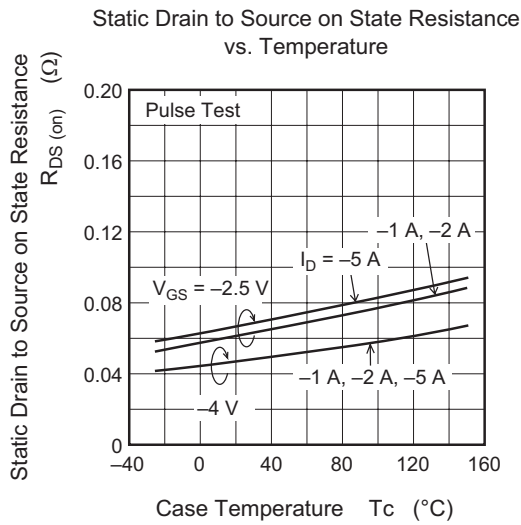
(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	V _{(BR) DSS}	-20	—	—	V	I _D = -10 mA, V _{GS} = 0
Gate to source breakdown voltage	V _{(BR) GSS}	±10	—	—	V	I _G = ±100 μA, V _{DS} = 0
Gate to source leak current	I _{GSS}	—	—	±10	μA	V _{GS} = ±8 V, V _{DS} = 0
Zero gate voltage drain current	I _{DSS}	—	—	-10	μA	V _{DS} = -20 V, V _{GS} = 0
Gate to source cutoff voltage	V _{GS (off)}	-0.5	—	-1.5	V	V _{DS} = -10 V, I _D = -1 mA
Static drain to source on state resistance	R _{DS (on)}	—	0.048	0.060	Ω	I _D = -3 A, V _{GS} = -4 V ^{Note 3}
	R _{DS (on)}	—	0.065	0.085	Ω	I _D = -3 A, V _{GS} = -2.5 V ^{Note 3}
Forward transfer admittance	y _{fs}	6	9.5	—	S	I _D = -3 A, V _{DS} = -10 V ^{Note 3}
Input capacitance	C _{iss}	—	1200	—	pF	V _{DS} = -10 V
Output capacitance	C _{oss}	—	630	—	pF	V _{GS} = 0
Reverse transfer capacitance	C _{rss}	—	200	—	pF	f = 1 MHz
Turn-on delay time	t _{d (on)}	—	20	—	ns	V _{GS} = -4 V, I _D = -3 A,
Rise time	t _r	—	120	—	ns	V _{DD} ≅ -10 V
Turn-off delay time	t _{d (off)}	—	175	—	ns	
Fall time	t _f	—	140	—	ns	
Body-drain diode forward voltage	V _{DF}	—	-0.9	-1.4	V	I _F = -5.5 A, V _{GS} = 0 ^{Note 3}
Body-drain diode reverse recovery time	t _{rr}	—	65	—	ns	I _F = -5.5 A, V _{GS} = 0 di _F /dt = 20 A/μs

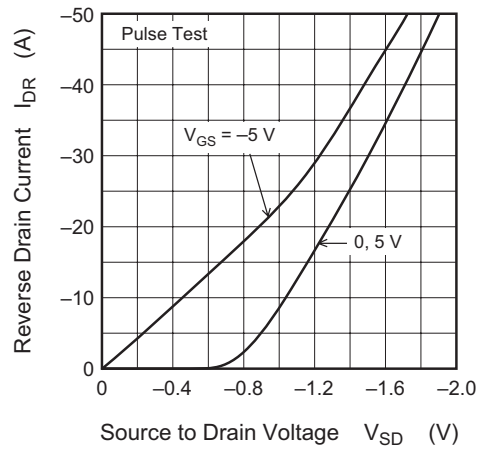
Note: 3. Pulse test

Main Characteristics

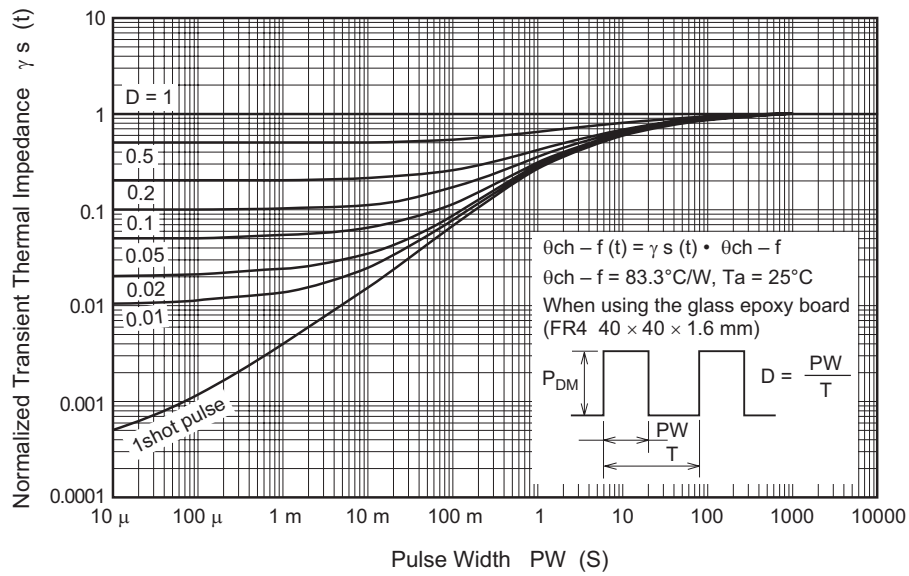




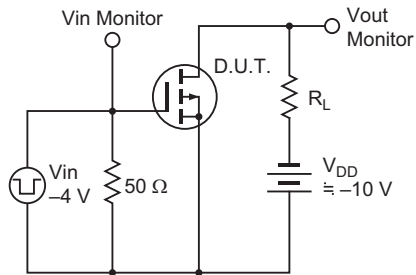
Reverse Drain Current vs. Source to Drain Voltage



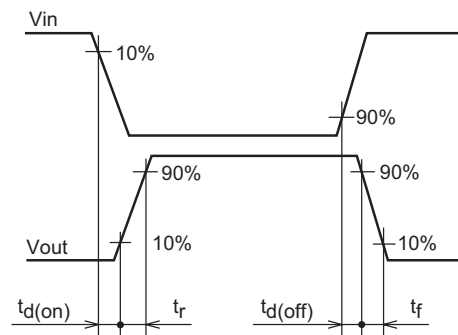
Normalized Transient Thermal Impedance vs. Pulse Width



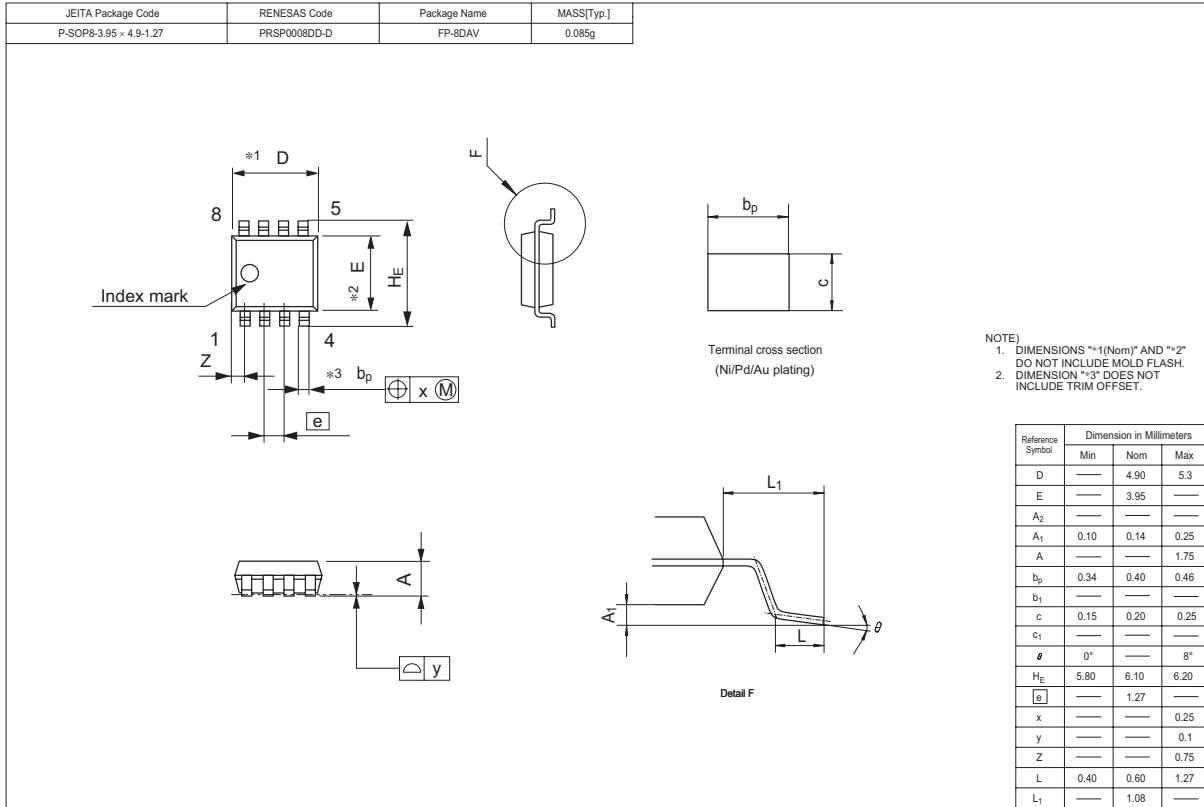
Switching Time Test Circuit



Switching Time Waveform



Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
HAT1021R-EL-E	2500 pcs	Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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